



3DA10

NPN Silicon High Frequency High Power Transistor



Features:

1. Excellent second breakdown capacity. Good characteristic frequency.
2. Amplification factor of small current is great. Good voltage resistance.
3. Implementation of standards: GJB33 A-97, QZJ840611A, QZJ840611
4. Use for analog computer power output, amplification of high frequency,middle frequency and low frequency, switching circuit.
5. Quality Class: JP, JT, JCT, GS, G, G+

TECHNICAL DATA:

(Ta = 25°C)

Parameter name	Symbols	Unit	Specifications							Test Condition
			A	B	C	D	E	F	G	
Total Dissipation	P _{tot}	W	10							Tc:75°C
Max. Collector Current	I _{CM}	A	1							
Junction Temperature	T _{jm}	°C	175							
Storage Temperature	T _{stg}	°C	-55~+175							
C-B Breakdown Voltage	V _{(BR)CBO}	V	25	50	100	150	200	250	300	I _c =1mA
C-E Breakdown Voltage	V _{(BR)CEO}	V	25	50	100	150	200	250	300	I _c =1mA
E-B Breakdown Voltage	V _{(BR)EBO}	V	4							I _E =1mA
Collector- Emitter Saturation Voltage Drop	V _{CE(sat)}	V	1.5							I _c =0.5A, I _B =0.1A
Collector-Base Leakage Current	I _{CBO}	mA	0.5							V _{CB} =20V
Collector-Emitter Leakage Current	I _{CEO}	mA	1.0							V _{CE} =20V
Base-Emitter Leakage Current	I _{BEO}	mA	2.0							V _{EB} =2V
DC Current Gain	h _{FE}		Red:15~25		Orange:25~40		Yellow:40~55			V _{CE} =5V, I _c =0.5A
			Green:55~80		Blue:80~120		Purple:120~180			
Transition frequency	f _T	MHz	30							V _{CE} =10V, I _c =0.5A f _o =10 MHz

Outline and Dimensions: